

IRF540NS

IRF540NL

HEXFET® Power MOSFET

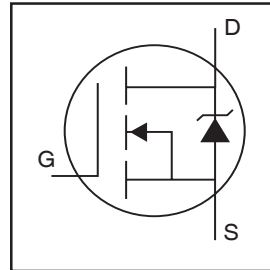
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

Description

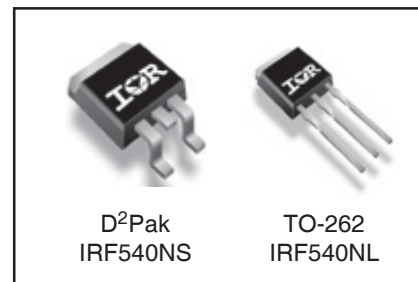
Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF540NL) is available for low-profile applications.



$V_{DSS} = 100V$
$R_{DS(on)} = 44m\Omega$
$I_D = 33A$



D²Pak
IRF540NS

TO-262
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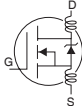
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ⑦	33	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ⑦	23	
I_{DM}	Pulsed Drain Current ① ⑦	110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	130	W
	Linear Derating Factor	0.87	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current ①	16	A
E_{AR}	Repetitive Avalanche Energy ①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑦	7.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.15	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/°C	Reference to 25°C, I _D = 1mA ⑦
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	44	mΩ	V _{GS} = 10V, I _D = 16A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	21	—	—	S	V _{DS} = 50V, I _D = 16A②⑦
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 100V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	71	nC	I _D = 16A
Q _{gs}	Gate-to-Source Charge	—	—	14		V _{DS} = 80V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	21		V _{GS} = 10V, See Fig. 6 and 13 ④⑦
t _{d(on)}	Turn-On Delay Time	—	11	—	ns	V _{DD} = 50V
t _r	Rise Time	—	35	—		I _D = 16A
t _{d(off)}	Turn-Off Delay Time	—	39	—		R _G = 5.1Ω
t _f	Fall Time	—	35	—		V _{GS} = 10V, See Fig. 10 ④⑦
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	1960	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	250	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	40	—		f = 1.0MHz, See Fig. 5 ⑦
E _{AS}	Single Pulse Avalanche Energy②⑦	—	700③	185⑥		mJ

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	33	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode)①	—	—	110		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 16A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	115	170	ns	T _J = 25°C, I _F = 16A
Q _{rr}	Reverse Recovery Charge	—	505	760	nC	di/dt = 100A/μs ④⑦
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 1.5mH
R_G = 25Ω, I_{AS} = 16A. (See Figure 12)
- ③ I_{SD} ≤ 16A, di/dt ≤ 340A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This is a typical value at device destruction and represents operation outside rated limits.

⑥ This is a calculated value limited to T_J = 175°C.

⑦ Uses IRF540N data and test conditions.

**When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

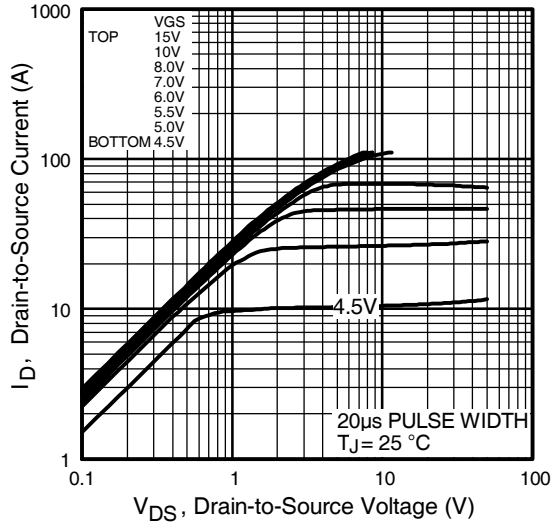


Fig 1. Typical Output Characteristics

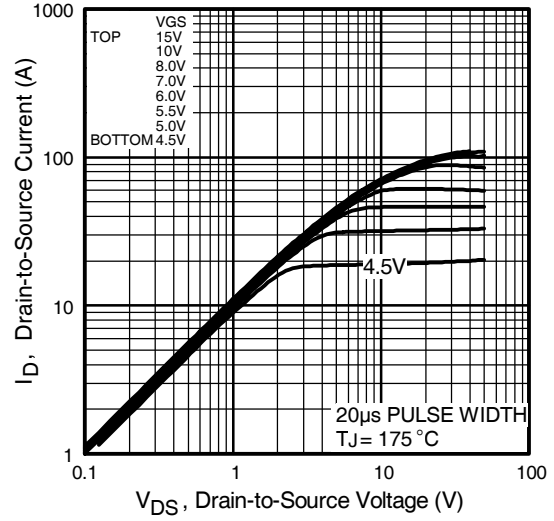


Fig 2. Typical Output Characteristics

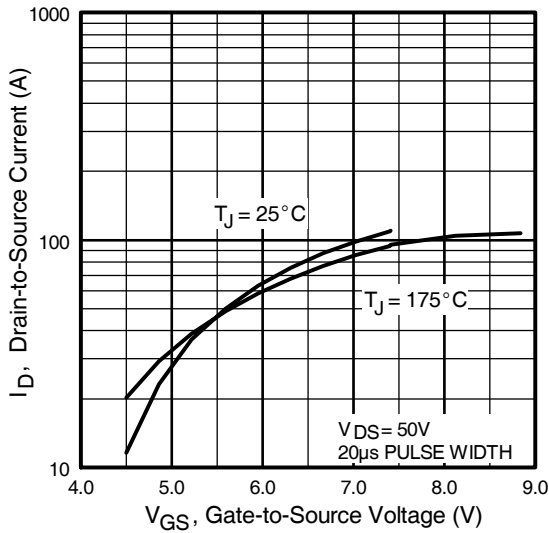


Fig 3. Typical Transfer Characteristics

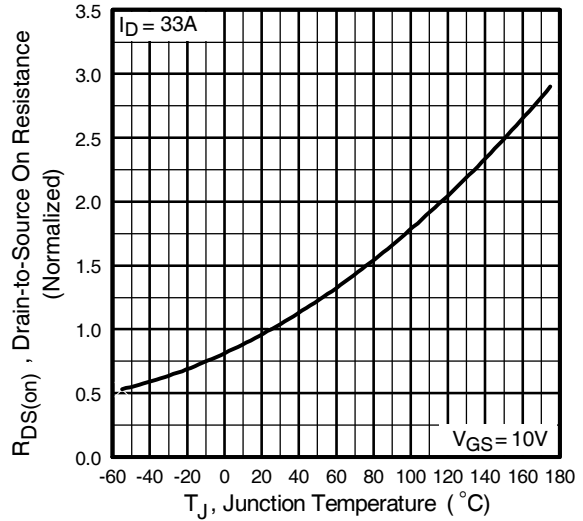


Fig 4. Normalized On-Resistance Vs. Temperature

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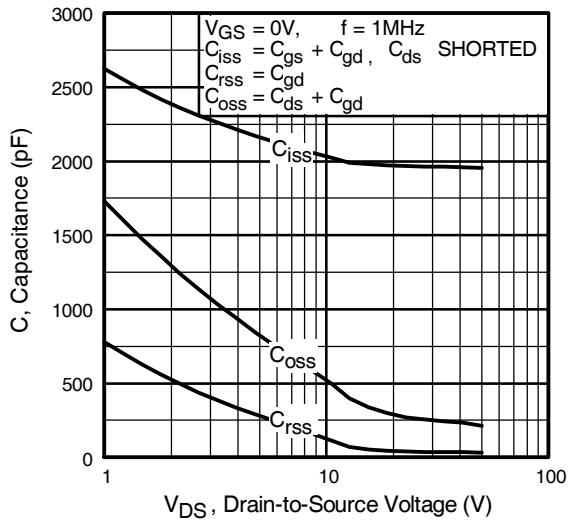


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

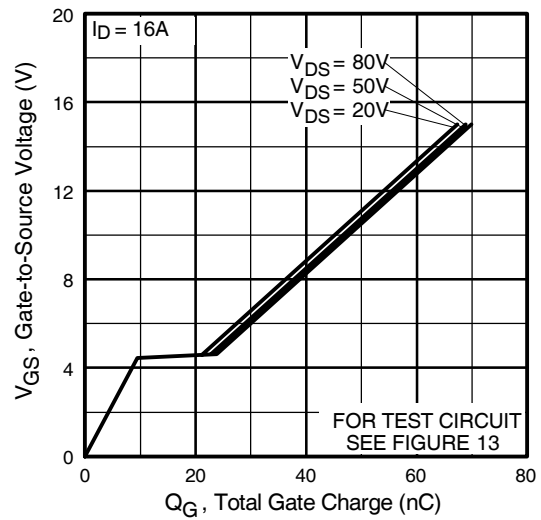


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

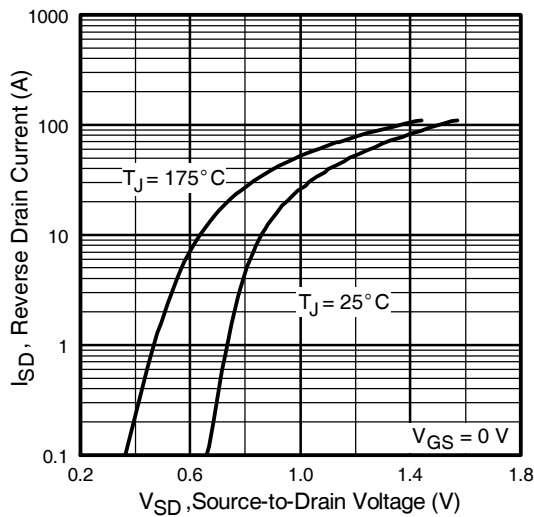


Fig 7. Typical Source-Drain Diode Forward Voltage

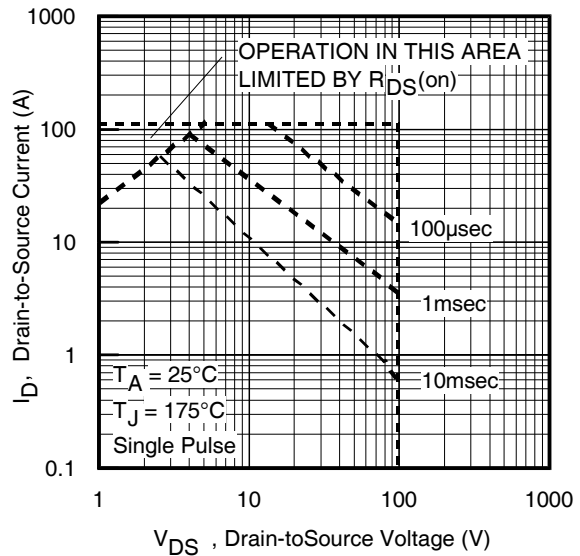


Fig 8. Maximum Safe Operating Area

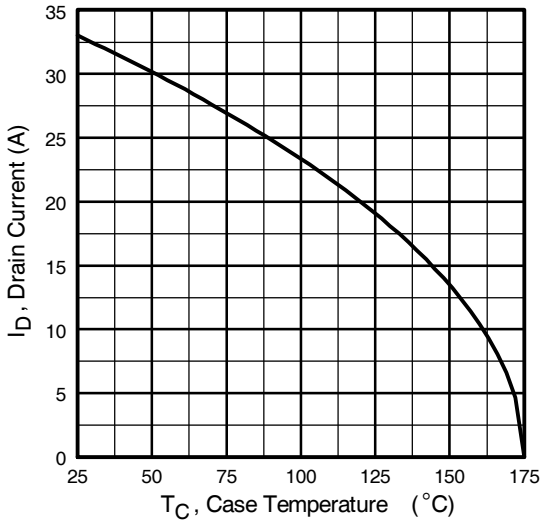


Fig 9. Maximum Drain Current Vs. Case Temperature

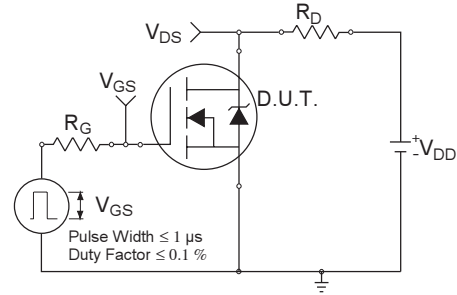


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

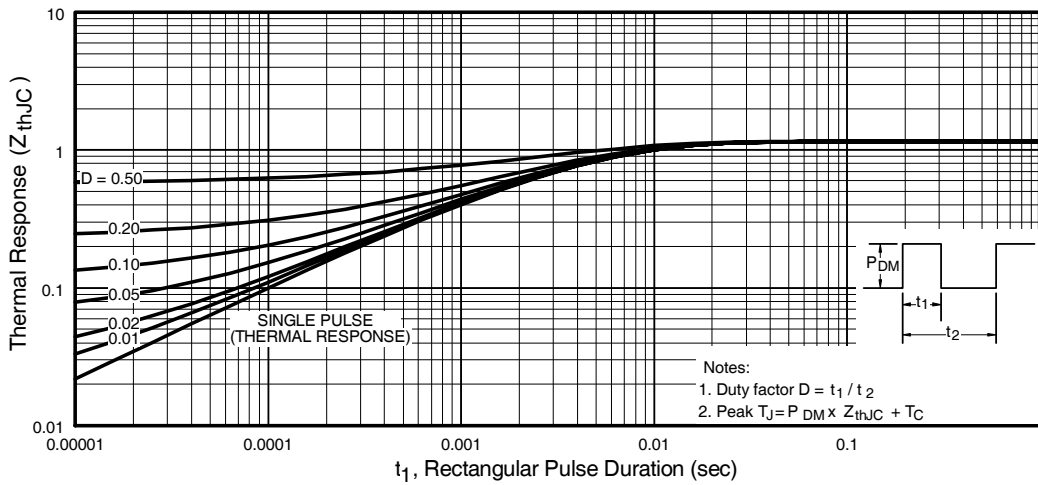


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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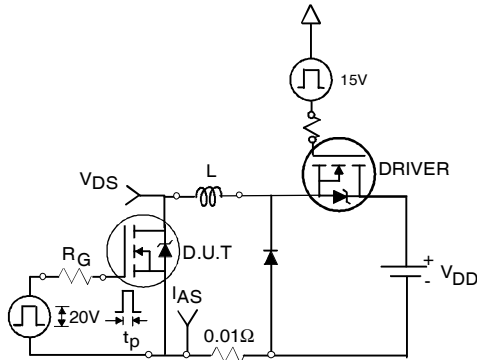


Fig 12a. Unclamped Inductive Test Circuit

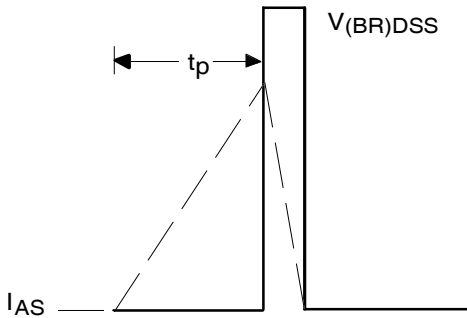


Fig 12b. Unclamped Inductive Waveforms

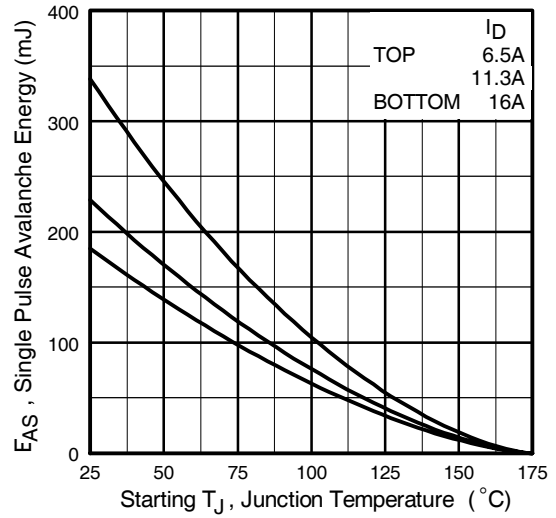


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

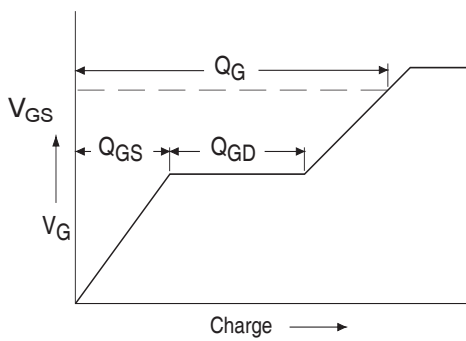


Fig 13a. Basic Gate Charge Waveform

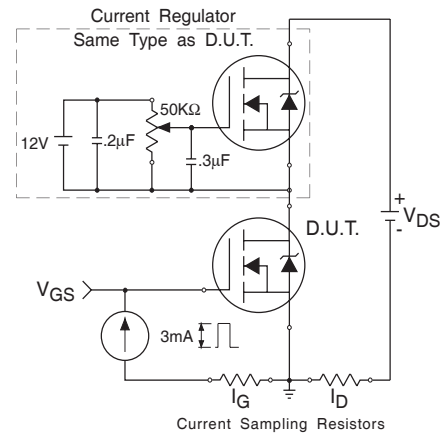


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel



*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

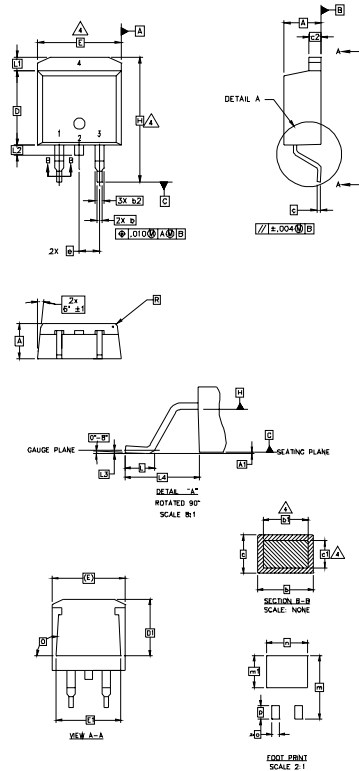
Fig 14. For N-channel HEXFET® power MOSFETs

IRF540NS/IRF540NL

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.06	4.83	.160	.190	4	
A1	0.00	0.254	.000	.010		
b	0.51	0.99	.020	.039		
b1	0.51	0.89	.020	.035		
b2	1.14	1.78	.045	.070		
c	0.38	0.74	.015	.029		
c1	0.38	0.58	.015	.023		
c2	1.14	1.65	.045	.065		
D	8.51	9.65	.335	.380		
D1	6.86		.270			
E	9.65	10.67	.380	.420	3	
E1	6.22		.245			
e	2.54 BSC		.100 BSC		IGBTs, CoPACK	
H	14.61	15.88	.575	.625		
L	1.78	2.79	.070	.110		
L1		1.65		.065		
L2	1.27	1.78	.050	.070		
L3	0.25 BSC		.010 BSC		DIODES	
L4	4.78	5.28	.188	.208		
m	17.78		.700			
m1	8.89		.350			
n	11.43		.450		1.- ANODE *	
o	2.08		.082			2, 4.- CATHODE
p	3.81		.150			
R	0.51	0.71	.020	.028	* PART DEPENDENT.	
theta	90°	93°	90°	93°		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

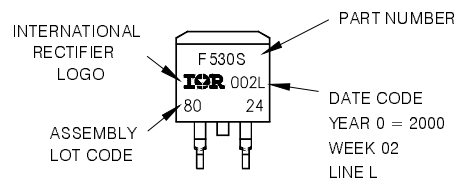
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

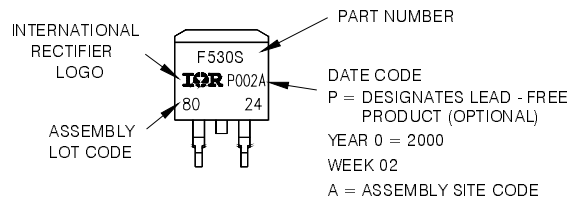
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE 'L'

Note: "P" in assembly line position
indicates "Lead - Free"

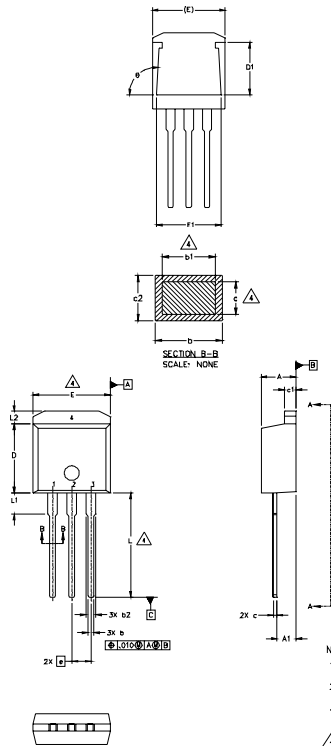


OR



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	3
D	8.51	9.65	.335	.380	
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

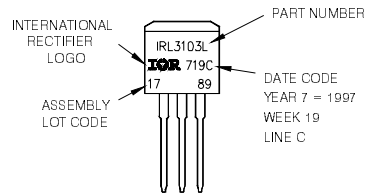
HEXFET	IGBT
1. - GATE	1 - GATE
2. - DRAIN	2 - COLLECTOR
3. - SOURCE	3 - EMITTER
4. - DRAIN	

NOTES

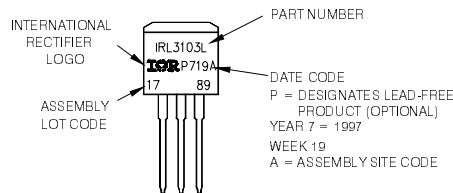
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2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE 'C'
 Note: 'P' in assembly line position indicates 'Lead-Free'



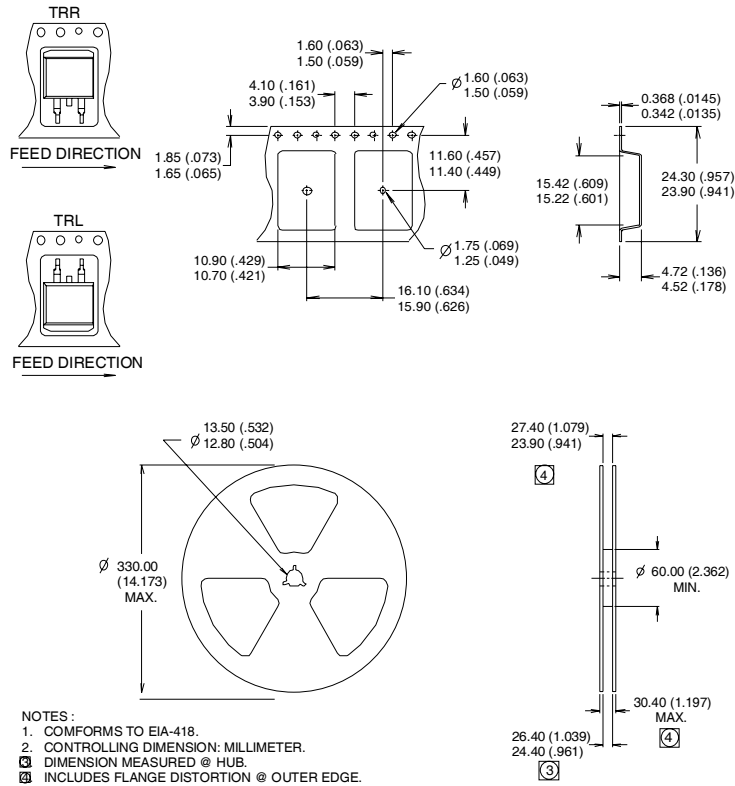
OR



IRF540NS/IRF540NL

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D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
 This product has been designed and qualified for the industrial market.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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 TAC Fax: (310) 252-7903

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